

## FEATURES

BROAD BAND INTERNALLY MATCHED FET

HIGH POWER

P1dB= 44.5dBm at 7.1GHz to 7.9GHz

HIGH GAIN

G1dB= 8.5dB at 7.1GHz to 7.9GHz

HERMETICALLY SEALED PACKAGE



## RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 5.2A f = 7.1 to 7.9GHz	dBm	43.5	44.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	7.5	8.5	—
Drain Current	IDS1		A	—	6.8	7.6
Gain Flatness	ΔG		dB	—	—	±0.6
Power Added Efficiency	ηadd		%	—	36	—
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 33.5dBm, f= 5MHz (Single Carrier Level)	dBc	-44	-47	—
Drain Current	IDS2		A	—	5.2	6.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	—	—	80

Recommended Gate Resistance(Rg): 28 Ω

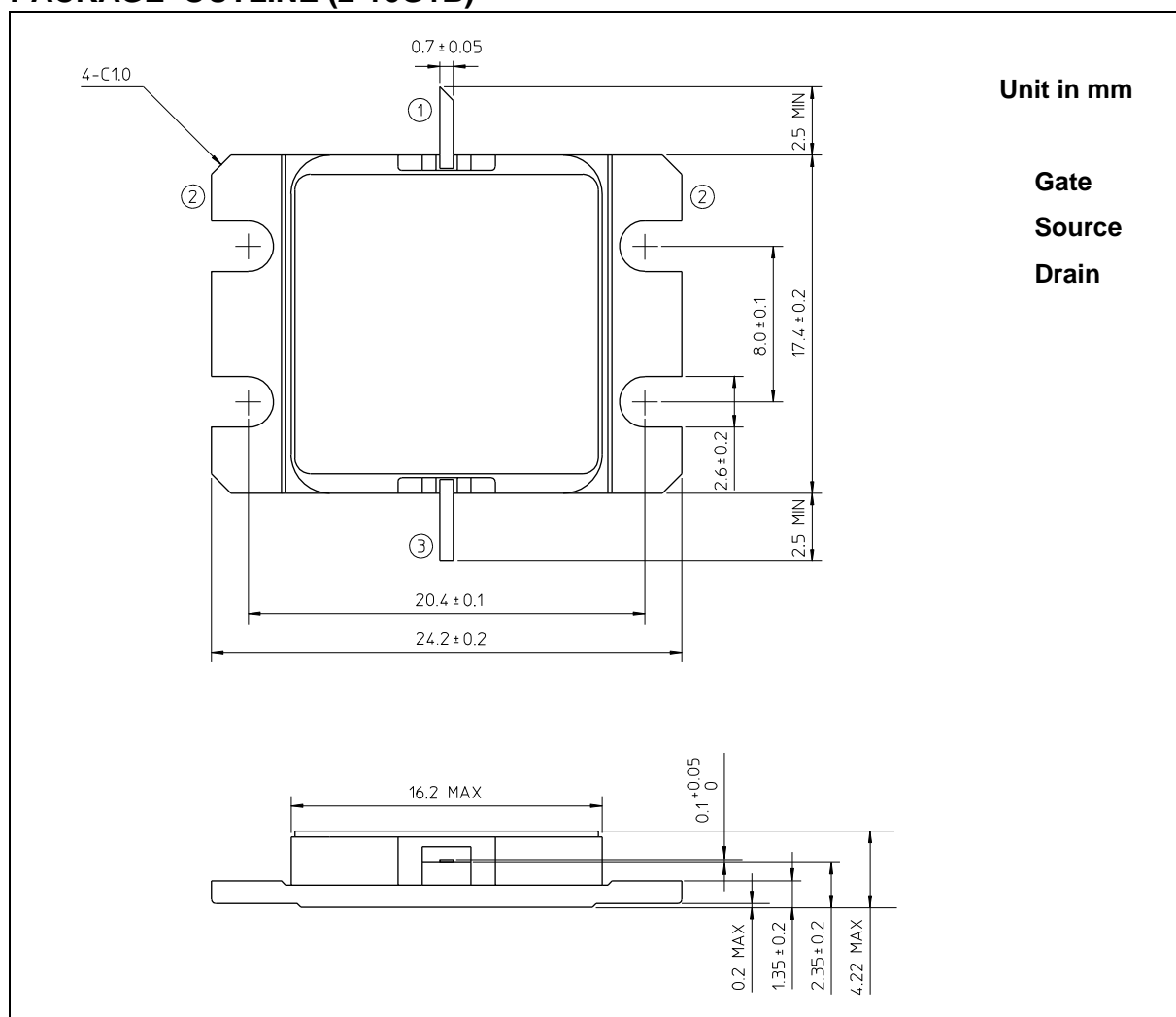
## ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 8.0A	S	—	5.0	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 80mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	14.4	—
Gate-Source Breakdown Voltage	VGSO	IGS= -280μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	1.2	1.5

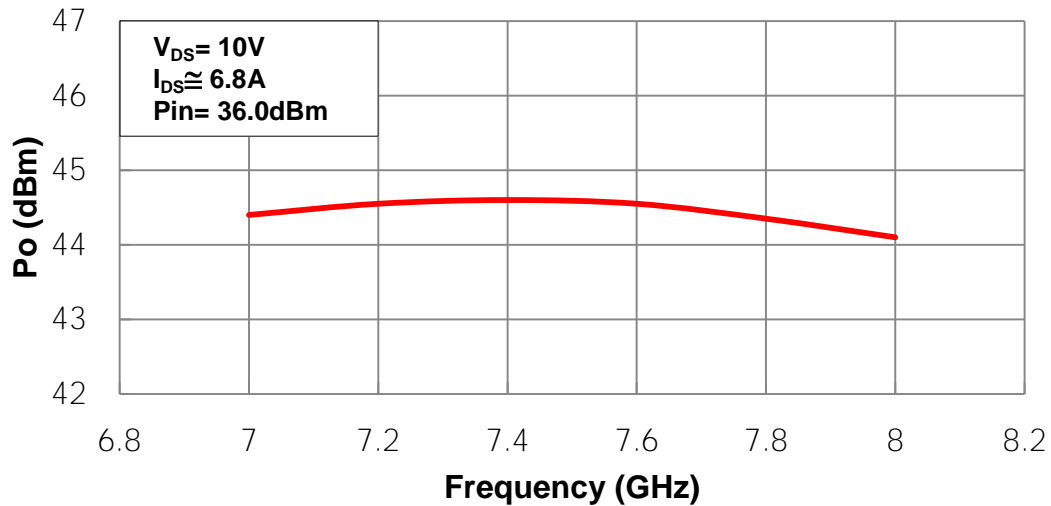
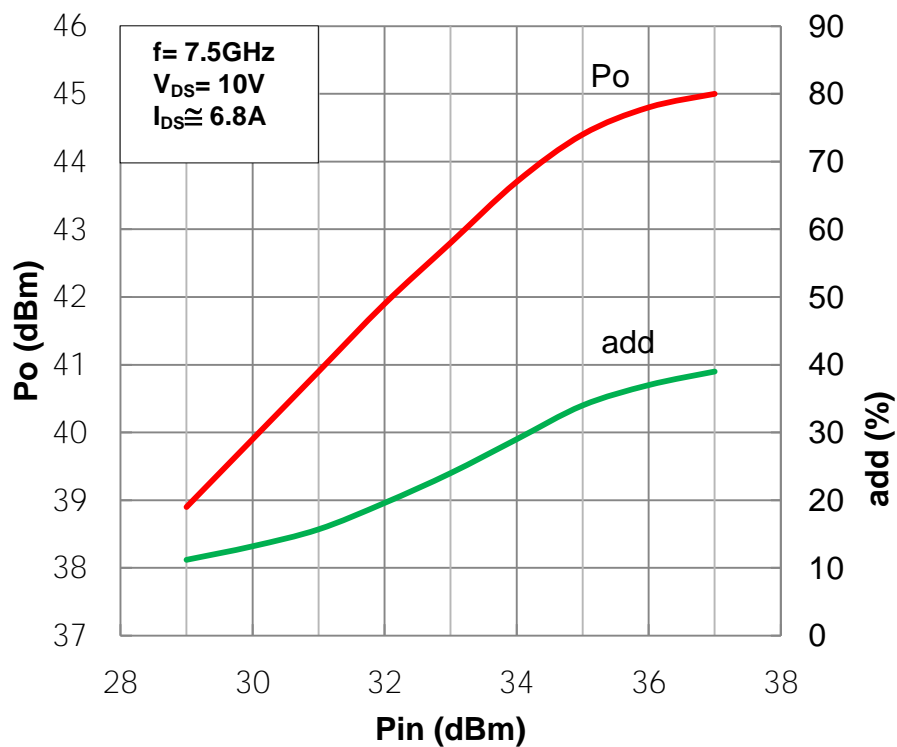
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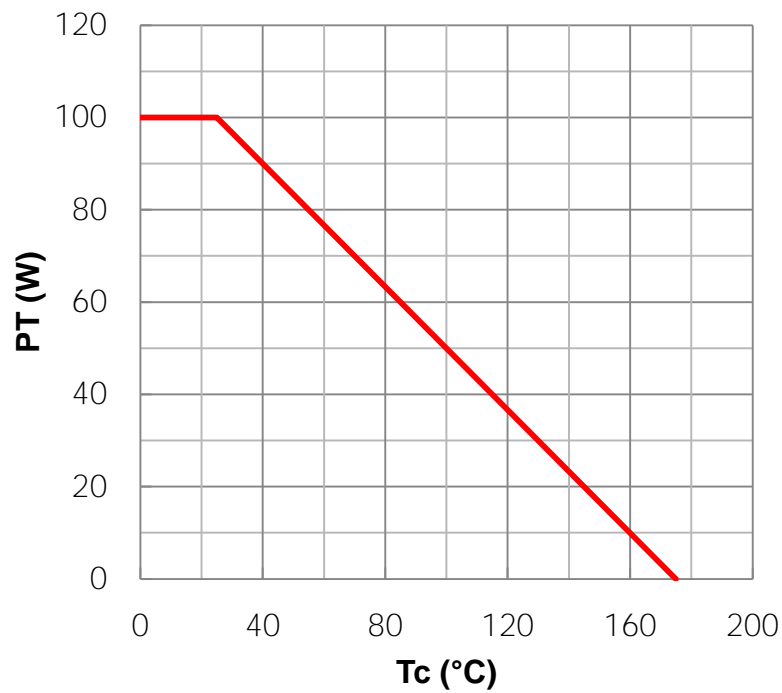
**ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)**

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	20.0
Total Power Dissipation (Tc= 25 °C)	PT	W	100
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

**PACKAGE OUTLINE (2-16G1B)**

**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

**RF PERFORMANCE**
**Output Power vs. Frequency**

**Output Power vs. Input Power**


**Power Dissipation vs. Case Temperature**

**IM3 vs. Output Power Characteristics**
